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U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	INVENTOR NAME	CLASS/ SUBCLASS	FILING DATE
FOREIGN PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES NO
OTHER PRIOR ART (including author, title, date, pertinent page, etc.)					
MLL		B. Prince, <u>Semiconductor Memories: A Handbook of Design, Manufacture, and Application</u> , 2nd edition, John Wiley & Sons, pp. 182-187, 07/1996.			
MLL		Weinberg, "On tunneling in metal-oxide-silicon structures", <u>J. Appl. Phys.</u> , v. 53, n. 7, pp. 5052-5056, 07/1982.			
MLL		Amin, "Design, selection, and implementation of flash erase EEPROM memory cells", <u>IEEE Proceedings-G</u> , v. 139, n. 3, pp. 370-376, 06/1992.			
MLL		Forbes, "Use of a spreadsheet for Fowler-Nordheim equation calculations", <u>J. Vac. Sci. Technol. B</u> , v. 17, n. 2, pp. 534-541, Mar/Apr. 1999.			
MLL		Lenzlinger et al., "Fowler-Nordheim Tunneling into Thermally Grown SiO ₂ ", <u>J. Appl. Phys.</u> , v. 40, n. 1, pp. 278-283, 01/1969.			
MLL		Masuoka et al., "Reviews and Prospects of Non-Volatile Semiconductor Memories", <u>IEICE Transactions</u> , v. E 74, n. 4, 04/1991.			
MLL		Masuoka et al., "Flash Memories, Their Status and Trends", <u>Proceedings of 4th Intl. Conf. on Solid-State and Integrated Circuit Technology</u> , pp. 128-132, 10/1995.			
MLL		Chi et al., "True Low-Voltage Flash Memory Operations", <u>Proceedings of 1996 Intl. Nonvolatile Memory Technology Conference</u> , pp. 94-98, 04/1996.			
DATE CONSIDERED 2/19/02		EXAMINER <i>Michael L. Lenzlinger</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

10/31/00